



STD78N75F4 STP78N75F4

N-channel 75 V, 0.0092 Ω , 78 A TO-220, DPAK
STripFET™ DeepGATE™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} max	I _D
STD78N75F4	75 V	< 0.011 Ω	70 A
STP78N75F4	75 V	< 0.011 Ω	78 A

- N-channel enhancement mode
- 100% avalanched rated
- Low gate charge
- Very low on-resistance

Application

- Switching applications

Description

This STripFET™ DeepGATE™ Power MOSFET technology is among the latest improvements, which have been especially tailored to minimize on-state resistance, with a new gate structure, providing superior switching performances.

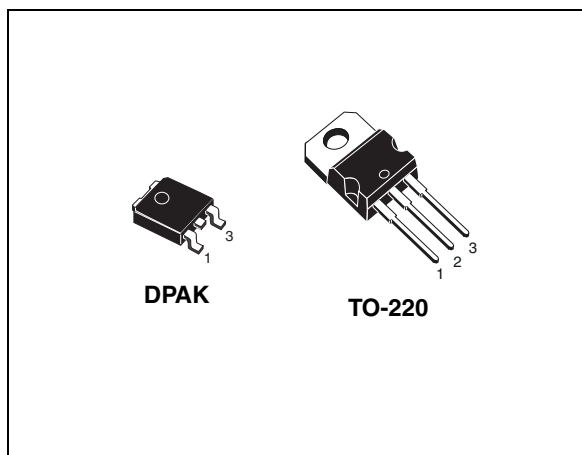
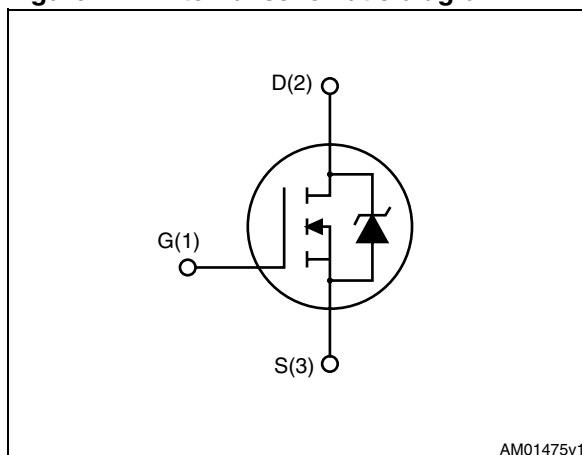


Figure 1. Internal schematic diagram



AM01475v1

Table 1. Device summary

Order codes	Marking	Package	Packaging
STD78N75F4	78N75F4	DPAK	Tape and reel
STP78N75F4	78N75F4	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220	DPAK	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	75		V
V_{GS}	Gate-source voltage	± 20		V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	78	70	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	55	50	A
$I_{DM}^{(1)}$	Drain current (pulsed)	312	280	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	150	125	W
	Derating factor	1	0.83	W/ $^{\circ}\text{C}$
$E_{AS}^{(2)}$	Single pulse avalanche energy	185		mJ
T_{stg}	Storage temperature	– 55 to 175		$^{\circ}\text{C}$
T_j	Operating junction temperature			

1. Pulse width limited by safe operating area

2. Starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = 35\text{ A}$, $V_{DD} = 50\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		TO-220	DPAK	
$R_{thj-case}$	Thermal resistance junction-case max	1	1.2	$^{\circ}\text{C}/\text{W}$
R_{thj-a}	Thermal resistance junction-ambient max	62.5		$^{\circ}\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max		50	$^{\circ}\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300		$^{\circ}\text{C}$

1. When mounted on FR-4 board of 1 inch², 2 oz Cu

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	75			V
I_{DSS}	Zero gate voltage Drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$ $V_{DS} = \text{max rating}$, $T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	For DPAK $V_{GS} = 10\text{ V}$, $I_D = 35\text{ A}$ For TO-220 $V_{GS} = 10\text{ V}$, $I_D = 39\text{ A}$		0.0092	0.011	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	5015	-	pF
C_{oss}	Output capacitance			382		pF
C_{rss}	Reverse transfer capacitance			218		pF
Q_g	Total gate charge	$V_{DD} = 37.5\text{ V}$, $I_D = 78\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 14)	-	76	-	nC
Q_{gs}	Gate-source charge			23		nC
Q_{gd}	Gate-drain charge			18.5		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD} = 37.5 \text{ V}$, $I_D = 39 \text{ A}$ $R_G = 4.7 \Omega$ $V_{GS} = 10 \text{ V}$ (see Figure 13)	-	25 33	-	ns ns
$t_{d(off)}$ t_f	Turn-off-delay time Fall time		-	61 14	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current	TO-220	-		78	A
		DPAK	-		70	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)	TO-220	-		312	A
		DPAK	-		280	A
$V_{SD}^{(2)}$	Forward on voltage	For TO-220 $I_{SD} = 78 \text{ A}$, $V_{GS} = 0$	-		1.5	V
		For DPAK $I_{SD} = 70 \text{ A}$, $V_{GS} = 0$				
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 78 \text{ A}$, $V_{DD} = 60 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s}$, $T_j = 150 \text{ }^\circ\text{C}$ (see Figure 15)	-	67 183 5.5		ns nC A

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

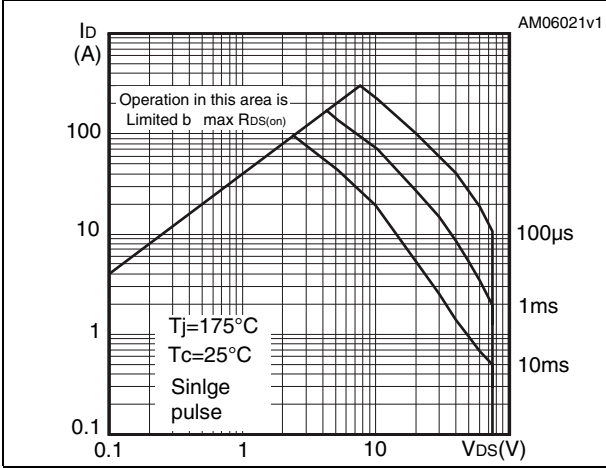


Figure 3. Thermal impedance

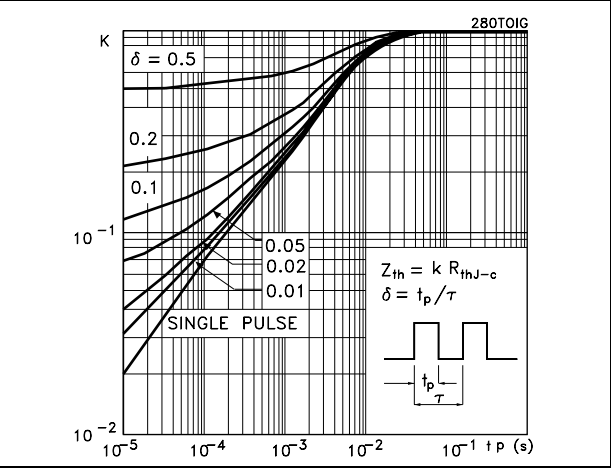


Figure 4. Output characteristics

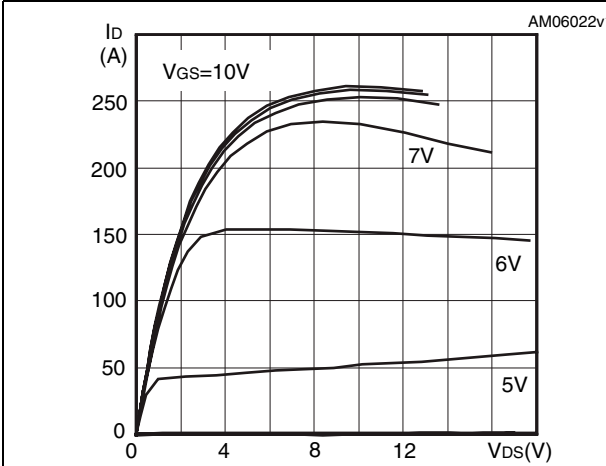


Figure 5. Transfer characteristics

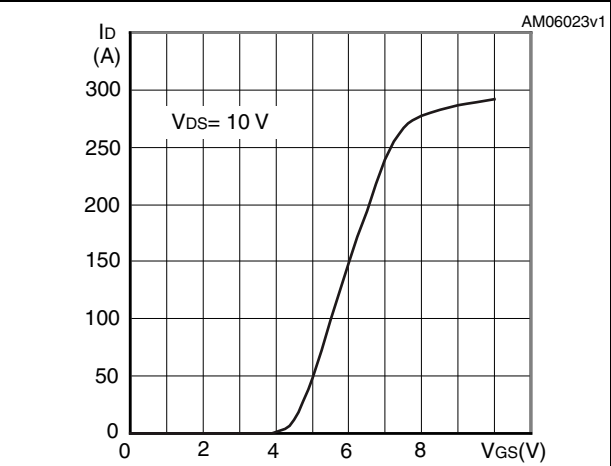


Figure 6. Normalized BV_{DSS} vs temperature

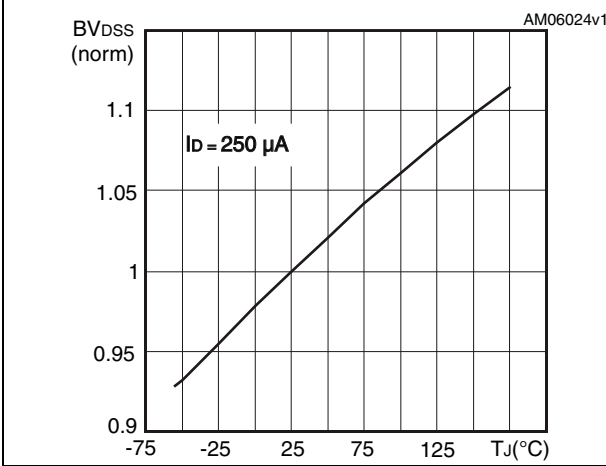


Figure 7. Static drain-source on resistance

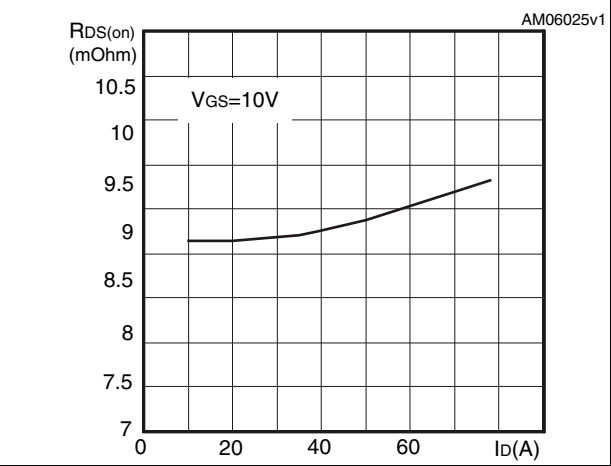


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

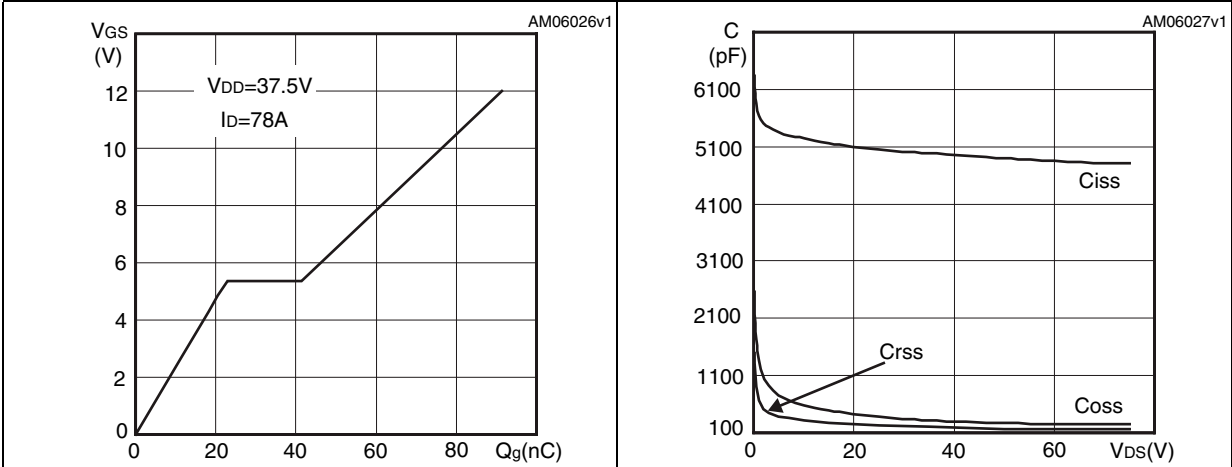


Figure 10. Normalized on resistance vs temperature

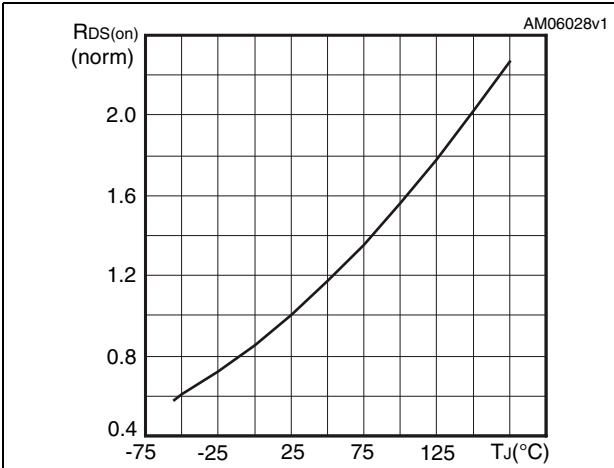


Figure 11. Normalized gate threshold voltage vs temperature

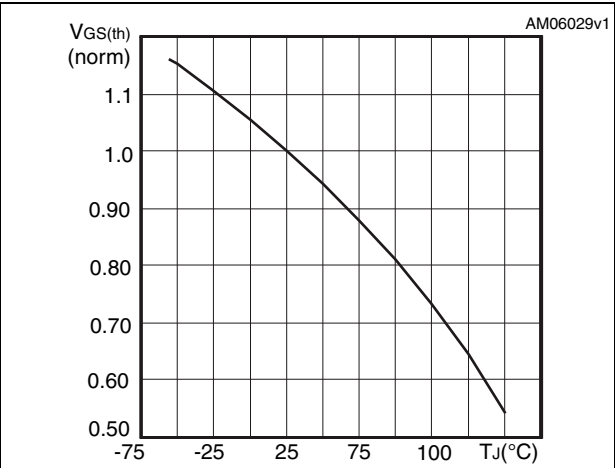
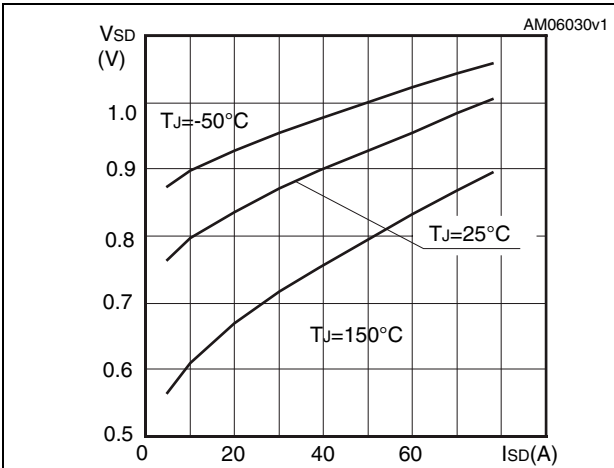


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

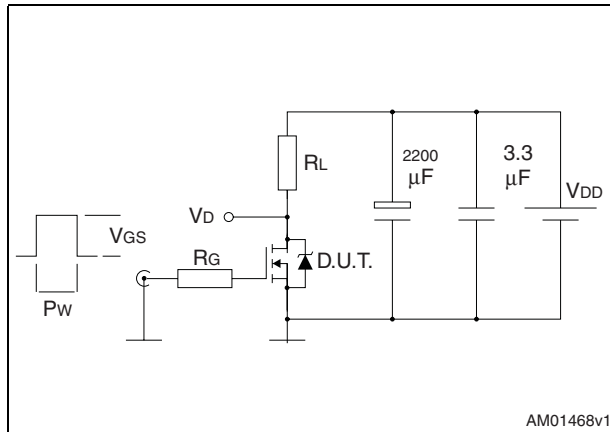


Figure 14. Gate charge test circuit

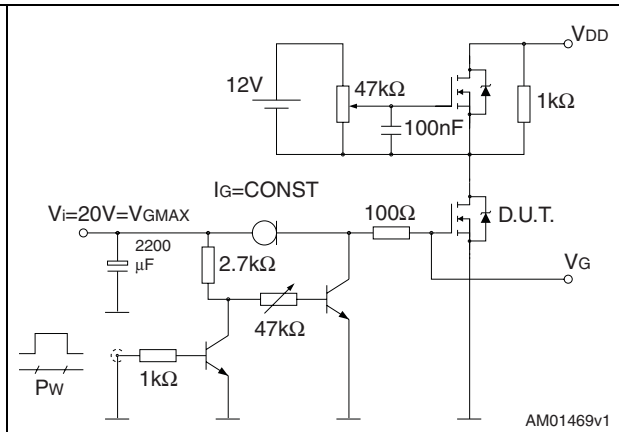


Figure 15. Test circuit for inductive load switching and diode recovery times

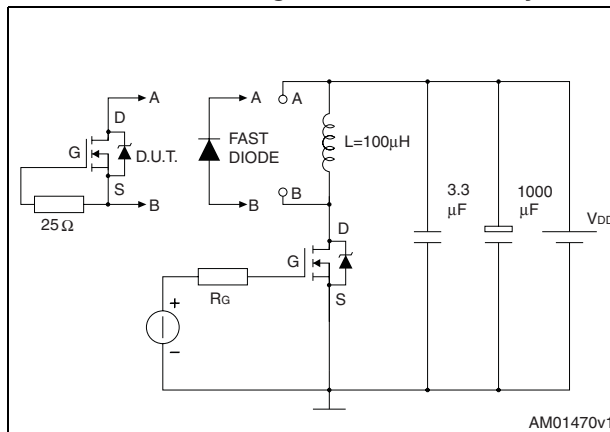


Figure 16. Unclamped inductive load test circuit

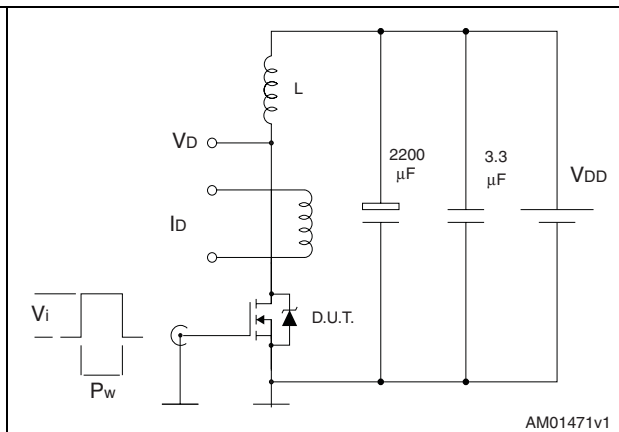


Figure 17. Unclamped inductive waveform

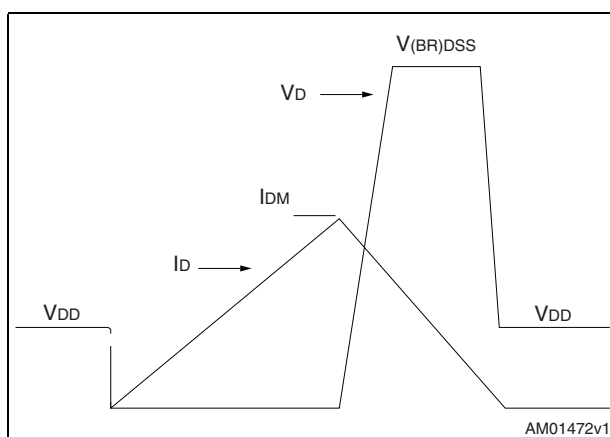
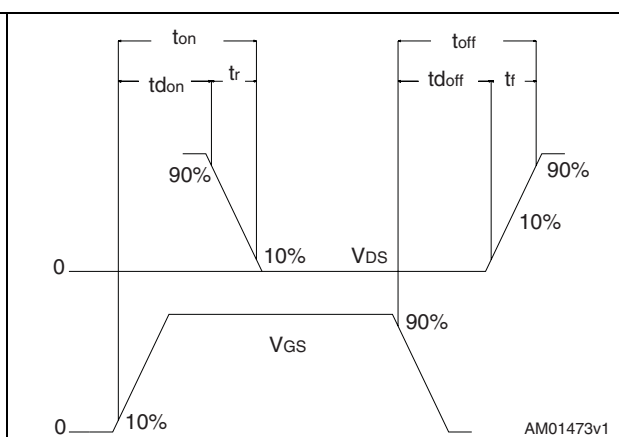


Figure 18. Switching time waveform

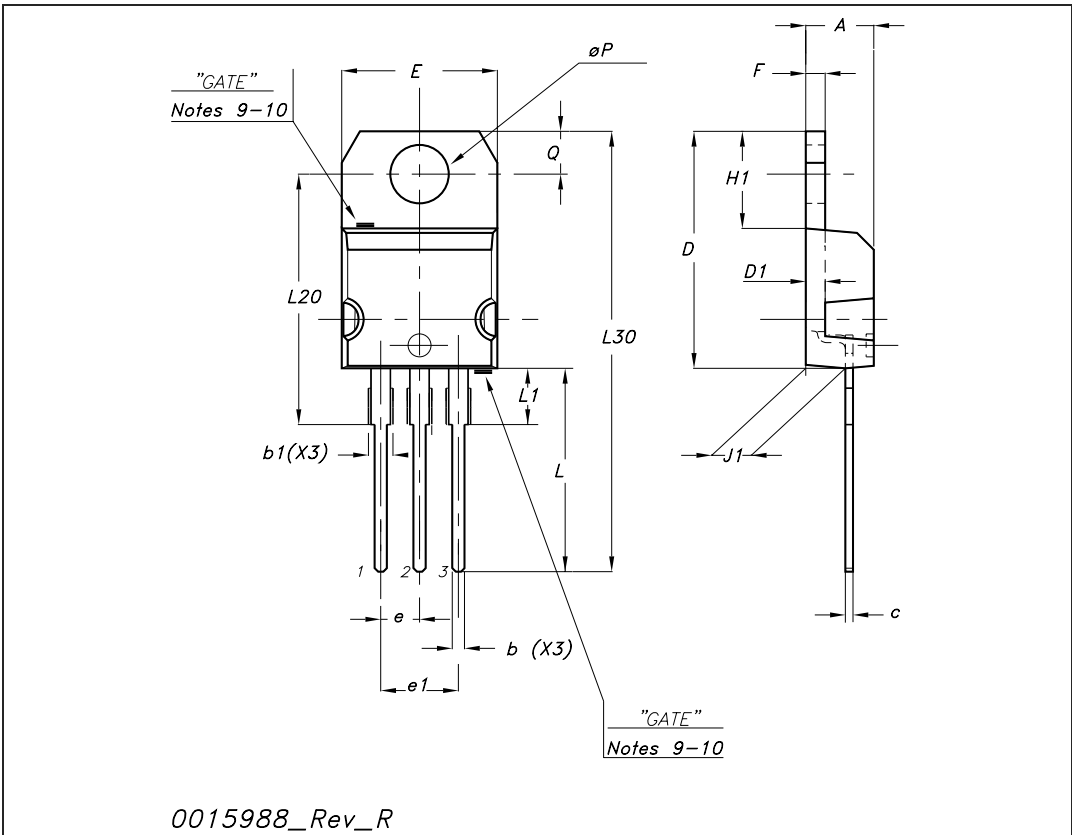


4 **Package mechanical data**

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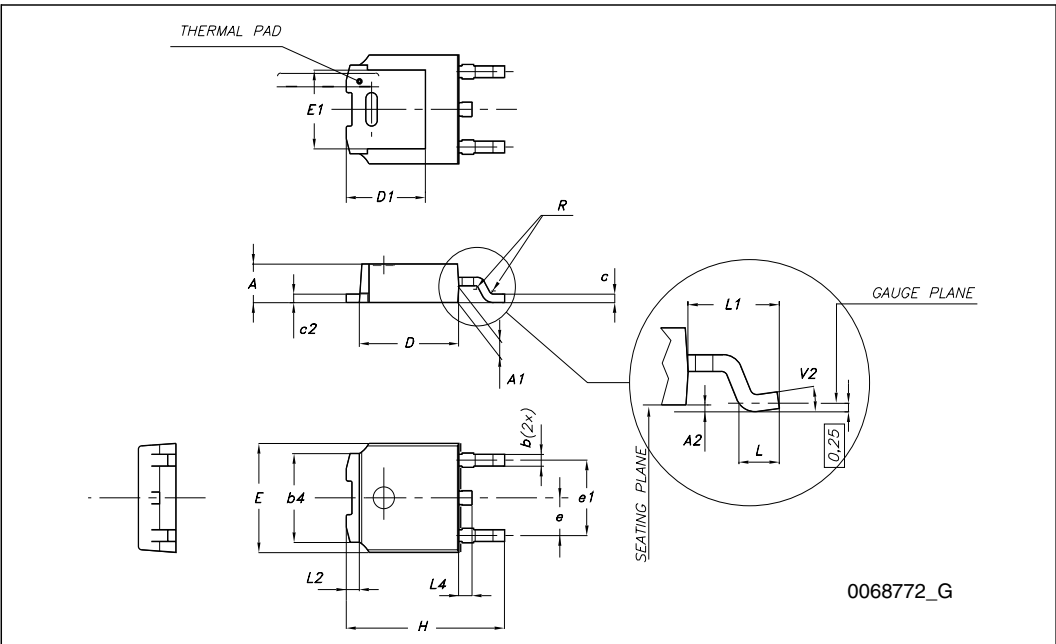
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116

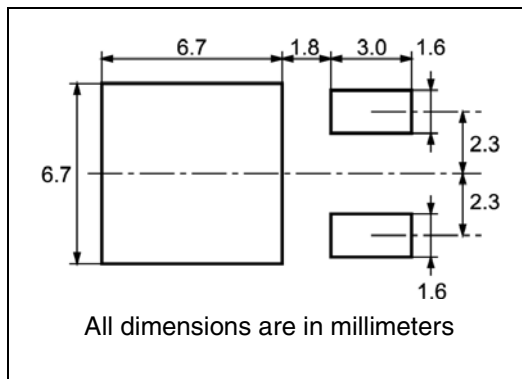


TO-252 (DPAK) mechanical data

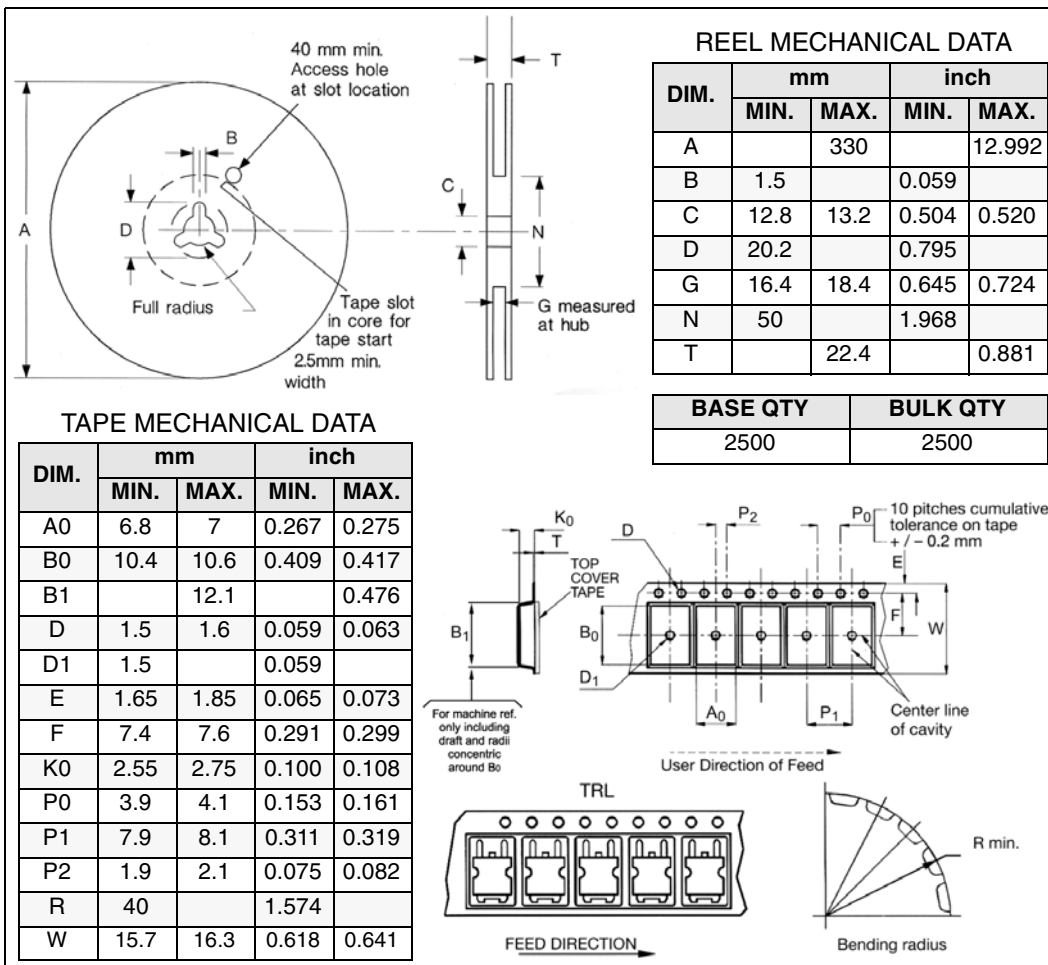
DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



DPAK FOOTPRINT



REEL MECHANICAL DATA



6 Revision history

Table 8. Document revision history

Date	Revision	Changes
12-May-2009	1	First release.
26-Nov-2009	2	Document status promoted from preliminary data to datasheet (see Section 2.1: Electrical characteristics (curves)).

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